

# DTC114TE NPN DIGITAL TRANSISTOR

#### **Features**

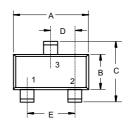
- Lead Free Finish/RoHS Compliant ("P" Suffix designates RoHS Compliant. See ordering information)
- Epoxy meets UL 94 V-0 flammability rating
- Moisure Sensitivity Level 1
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device design easy
- Halogen free available upon request by adding suffix "-HF"

#### **Mechanical Data**

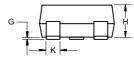
Case: SOT-523

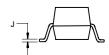


### SOT-523



Base
 Emitter
 Collector





DIMENSIONS									
	INCHES		MM						
DIM	MIN	MAX	MIN	MAX	NOTE				
Α	.059	.067	1.50	1.70					
В	.030	.033	0.75	0.85					
С	.057	.069	1.45	1.75					
D	.020 Nominal		0.50Nominal						
Е	.035	.043	0.90	1.10					
G	.000	.004	.000	.100					
Н	.028	.031	.70	0.80					
J	.004	.008	.100	.200					
K	.010	.014	.25	.35					

## Maximum Ratings and Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbol	Value	Unit	
Collector-Base Voltage	V <sub>CBO</sub>	50	V	
Collector-Emitter Voltage	$V_{\sf CEO}$	50	V	
Emitter-Base voltage	V <sub>EBO</sub>	5	V	
Collector Current-Continuous	Ic	100	mA	
Collector Dissipation	P <sub>C</sub>	150	mW	
Junction Temperature	TJ	150	$^{\circ}\! \mathbb{C}$	
Storage Temperature Range	T <sub>STG</sub>	-55~150	$^{\circ}\mathbb{C}$	

Parameter	Min	Тур	Max	Symbol	Unit
Collector-Base Breakdown Voltage (I <sub>C</sub> =50uA, I <sub>E</sub> =0)	50			V <sub>(BR)CBO</sub>	V
Collector-Emitter Breakdown Voltage (I <sub>C</sub> =1mA, I <sub>B</sub> =0)	50			V <sub>(BR)CEO</sub>	V
Emitter-Base Breakdown Voltage (I <sub>E</sub> =50uA, I <sub>C</sub> =0)	5			$V_{(BR)EBO}$	V
Collector Cut-off Current (V <sub>CB</sub> =50V, I <sub>E</sub> =0)			0.5	І <sub>сво</sub>	uA
Emitter Cut-off Current (V <sub>EB</sub> =4V, I <sub>C</sub> =0)			0.5	I <sub>EBO</sub>	uA
DC Current Gain (V <sub>CE</sub> =5V, I <sub>C</sub> =1mA)	100	300	600	h <sub>FE</sub>	
Collector-Emitter Saturation Voltage (I <sub>C</sub> =10mA, I <sub>B</sub> =1mA)			0.3	V <sub>CE(sat)</sub>	V
Input Resistor	7	10	13	R <sub>1</sub>	KΩ
Transition Frequency (V <sub>CE</sub> =10V, I <sub>C</sub> =-5mA, f=100MHz)		250		f <sub>T</sub>	MHz



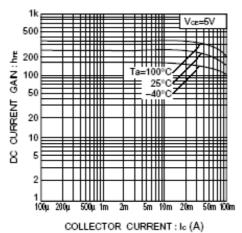


Fig.1 DC current gain vs. collector current

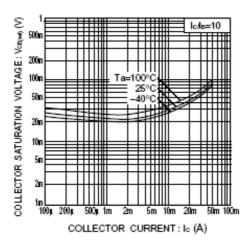


Fig.2 Collector-emitter saturation voltage vs. collector current